

/ Descriptions

WR0<50 P ММ Ё QSQ æ Ñ ç s ll 1 Silicon NPN transistor in a TO-92LM Plastic Package.

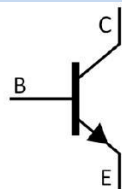
/ Features

т ³ я ¼ Н/лб 5VD9;7 Й ´ ' ё 5 Ъ 6 ³ ¼
Low $V_{CE(sat)}$,2 3W output in complementary pair with 2SA684.

/ Applications

т æ æ _ Ё | ' ё æ ³ ì 0
AF power amplifier and driver applications.

/ Equivalent Circuit



/ Pinning



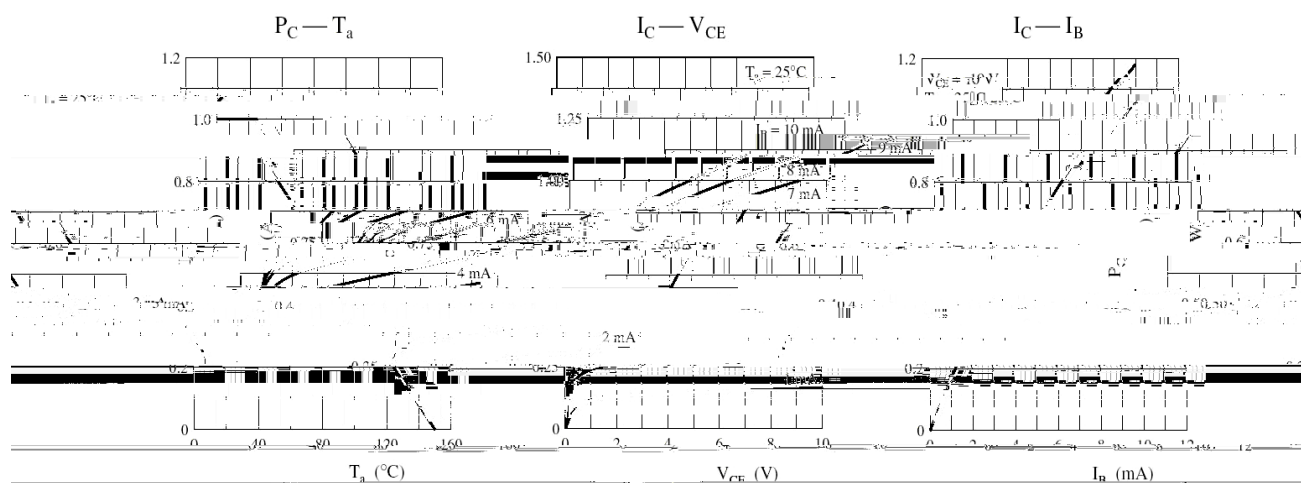
PIN1 χ Base PIN 2 χ Collector PIN 3 χ Emitter

/ h_{FE} Classifications & Marking

h_{FE} Classifications Symbol	Q	R	S
h_{FE} Range	85~170	120~240	170~340

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	60	V
Collector to Emitter Voltage	V_{CEO}	50	V
Emitter to Base Voltage	V_{EBO}	5.0	V
Collector Current - Continuous	I_C	1.0	A
Collector Current – Continuous(Pulse)	I_{CP}	1.5	A
Collector Power Dissipation	P_C	1.0	W
Junction Temperature	T_J	150	
Storage Temperature Range	T_{stg}	-55 150	°C

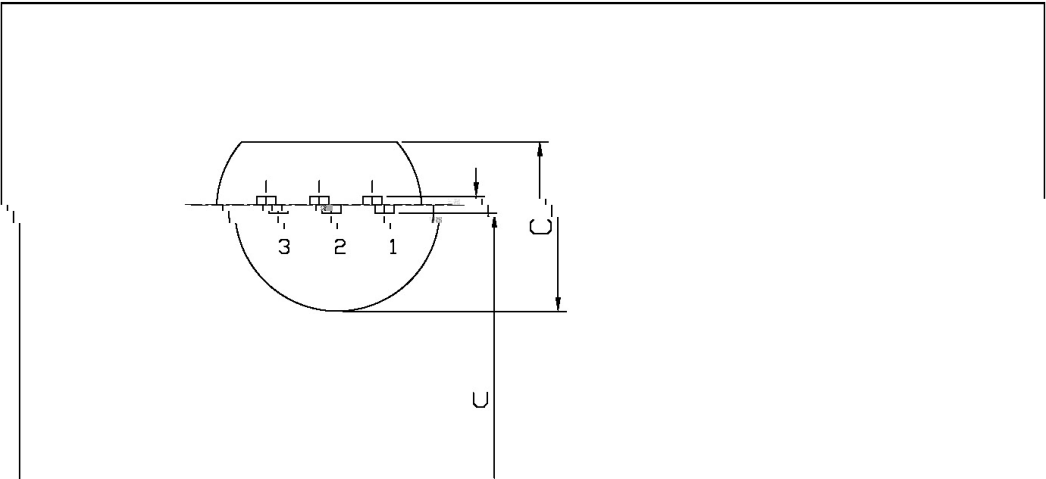
/ **Electrical Characteristic Curve**



/ Package Dimensions

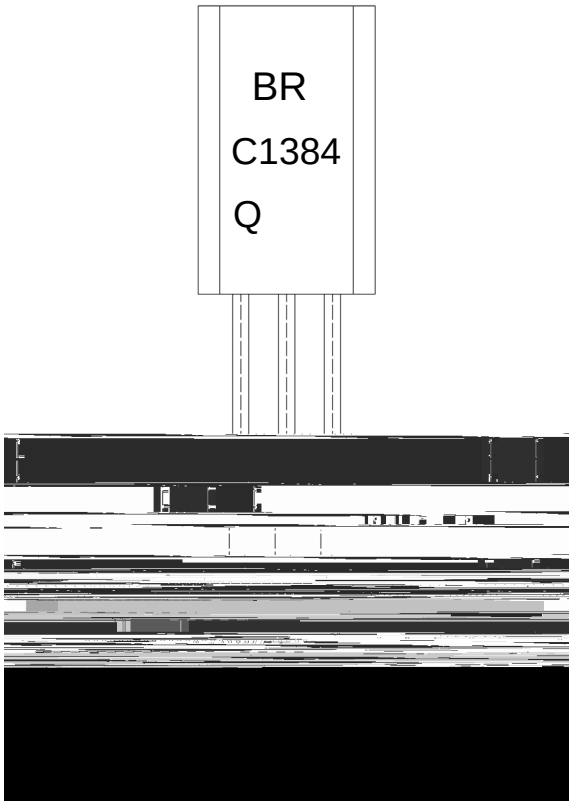
TO-92LM

Unit: mm



Symbol	Dimensions In Millimeters	
	Min	Max
A	4.7	5.1
B	1.2	1.5
C	0.8	1.0
D	0.5	0.6
E	0.4	0.5
F	0.3	0.4
G	0.2	0.3
H	0.1	0.2
I	0.1	0.2
J	0.1	0.2
K	0.1	0.2
L	0.1	0.2
M	0.1	0.2
N	0.1	0.2
O	0.1	0.2
P	0.1	0.2
Q	0.1	0.2
R	0.1	0.2
S	0.1	0.2
T	0.1	0.2
U	0.1	0.2
V	0.1	0.2
W	0.1	0.2
X	0.1	0.2
Y	0.1	0.2
Z	0.1	0.2

/ Marking Instructions



公司代码	公司代码
EU:	公司代码
F46;7	公司代码
T:	公司代码
----	公司代码
Note:	
BR:	Company Code.
C1384:	Product Type.
Q:	h _{FE} Classifications Symbol
****:	Lot No. Code,code change with Lot No.

() / Temperature Profile for Dip Soldering(Pb-Free)



б " X

1. 1. Preheating: 25~150 °C, Time: 60~90sec;
2. 2. Peak Temp.: 255 ± 5 °C, Duration: 5 ± 0.5sec;
3. 3. Cooling Speed: 2~10 °C/sec.

Note:

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3. Cooling Speed: 2~10 °C/sec.

/ Resistance to Soldering Heat Test Conditions

□ °C 270 ± 5 °C °C 10 ± 1 sec. Temp.: 270 ± 5 °C Time: 10 ± 1 sec

/ Packaging SPEC.

“Q” T Y E / BULK

Package Type	Units				Dimension		(unit mm3)